

IN THE SPECIFICATION:

Page 3, delete the whole paragraph starting in line 18 and replace it with the following new paragraph:

---The semiconductor device according to the present invention includes the low-resistance layer provided under the interconnection extending from the signal input, whereby the substrate resistance is decreased by this low-resistance layer, the heat noises caused by the substrate resistance can be reduced, and the noise characteristic of the semiconductor device can also be improved.---

See the attached Appendix for the changes made to effect the above paragraph.

Page 3, delete the whole paragraph starting in line 18 and replace it with the following new paragraph:

---Next, a gate oxide layer 123 is provided in the device region by thermal oxidation, polysilicon is deposited thereon, and patterning is effected thereon, thereby obtaining a gate electrode 107 (FIG. 4). In an example shown in FIG. 4, the gate electrode and an impurity diffused region peripheral to this gate electrode take a well-known LDD structure. To be specific, after providing the gate electrode 107, with the gate electrode serving as an ion implantation mask, ions are implanted into the device region by a comparatively low energy, whereby a low-concentration diffused layer 131 is formed shallow. Subsequently, insulating layers such as silicon nitride layer and silicon oxide layer are deposited on the whole and etched back by an anisotropic etching method, whereby a side wall 132 is provided on a side surface of the gate electrode. With this side wall 132 serving as a mask, the ions are implanted by a comparatively high energy, whereby a high-concentration diffused layer 133 is